

Amendments to the Specification

Please replace the paragraph bridging pages 14 and 15 with the following:

Further layers of the upper metal scheme may subsequently be formed. First, another polymer layer 222 is deposited and patterned to form via 223. Two alternatives may then be used to fill the via and form interconnecting lines. First, a dual damascene method is used, such as ~~partially~~ shown in Fig. 21b, in which a second polymer layer 224 is deposited and patterned to form interconnecting line opening 225. Subsequent processing (~~not shown~~) then takes place, as described above, by forming adhesion layer 252, forming a and seed layers, plating metal layer 254, and CMP to complete the interconnecting line. The second method is ~~partially~~ shown in Fig. 21c, in which via 223 is first filled with adhesion and seed layers 226, and then via metal 227 is electroplated and planarized using CMP. Then second polymer 224 is deposited, and patterned as shown, and then filled with adhesion layer 256 and metal 258 and planarized, to form interconnecting lines (~~not shown~~).